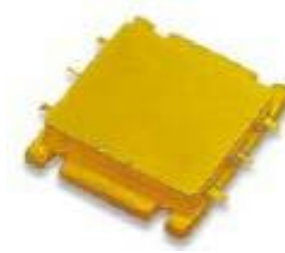


Performance

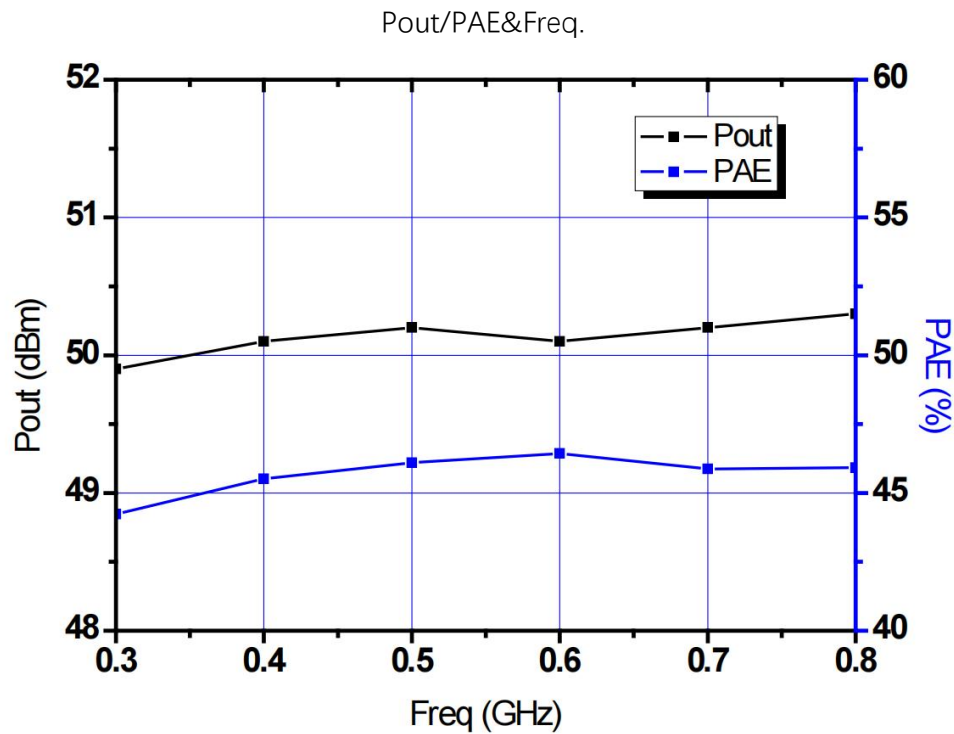
- Technology: 0.5um Power GaN HEMT
- Frequency: 0.3~0.8GHz
- Typical Pout : 50dBm(CW)
- Typical Gain: 10dB
- Typical PAE: 45%
- Bias: 28V/-2~-3V a certain point
- Package: Metal Ceramic



Electrical Specifications (TA=25°C, Vd=28V, Pin=40dBm, F: 0.3~0.8GHz)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	49.5	50	-	dBm
Gp	Power Gain	9.5	10	-	dB
η_{add}	Power Added Efficiency	43	45	-	%
ΔGp	Gain Flatness	-1.5	-	+1.5	dB

Test Curves

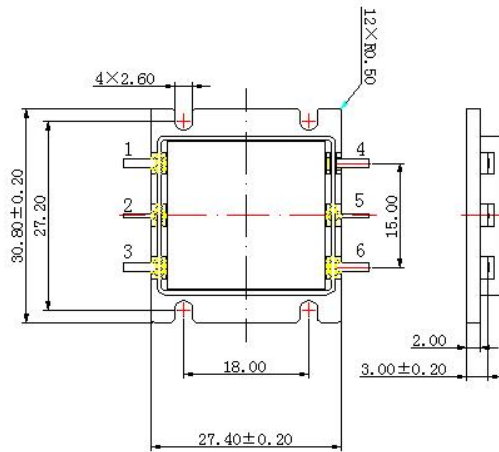


Absolute Max Ratings (T_A=25°C)

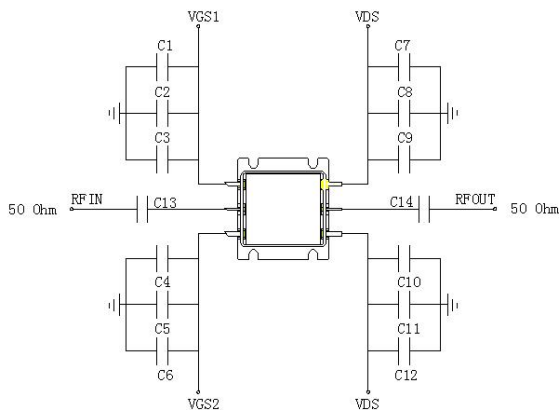
Symbol	Parameter	Value	Remark
V _d	Drain Voltage	40V	
V _g	Grid Voltage	-5V	
P _d	DC Dissipation	220W	25°C
T _{ch}	Channel Temperature	225°C	【1】
T _m	Mounting Temperature	300°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~175°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing



Application Circuit



Symbol	Value
C1/C4	100pF
C2/C5	1000pF
C3/C6	10uF
C7/C10	100pF
C8/C11	1000pF
C9/C12	47uF
C13	20pF
C14	20pF

Note:

- (1) V_{G1}=V_{G2}=V_{GS};
- (2) Power module power-on sequence: V_{G1}, V_{G2}, V_{DS};
- (3) Power-off sequence of power modules: V_{DS}, V_{G2}, V_{G1}